February 1999



# FDN360P Single P-Channel PowerTrench<sup>™</sup> MOSFET

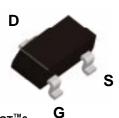
### **General Description**

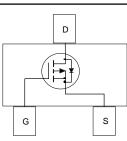
This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

### Applications

- DC/DC converter
- Load switch
- Motor drives





• -2 A, -30 V.  $R_{DS(on)} = 0.080 \ \Omega @ V_{GS} = -10 \ V$ 

• High performance trench technology for extremely

• High power and current handling capability.

• Low gate charge (5nC typical).

• Fast switching speed.

low R<sub>DS(ON)</sub>.

 $R_{DS(on)} = 0.125 \ \Omega \ @ V_{GS} = -4.5 \ V.$ 

SuperSOT<sup>™</sup>-3

## Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-30	V
V <sub>GSS</sub>	Gate-Source Voltage		<u>+</u> 20	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a)		-2	А
	- Pulsed		-20	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)		0.5	W
		(Note 1b)	0.46	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range		-55 to +150	۰C

**Features** 

# Thermal Characteristics

R <sub>θ</sub> JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R <sub>θ</sub> JC	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

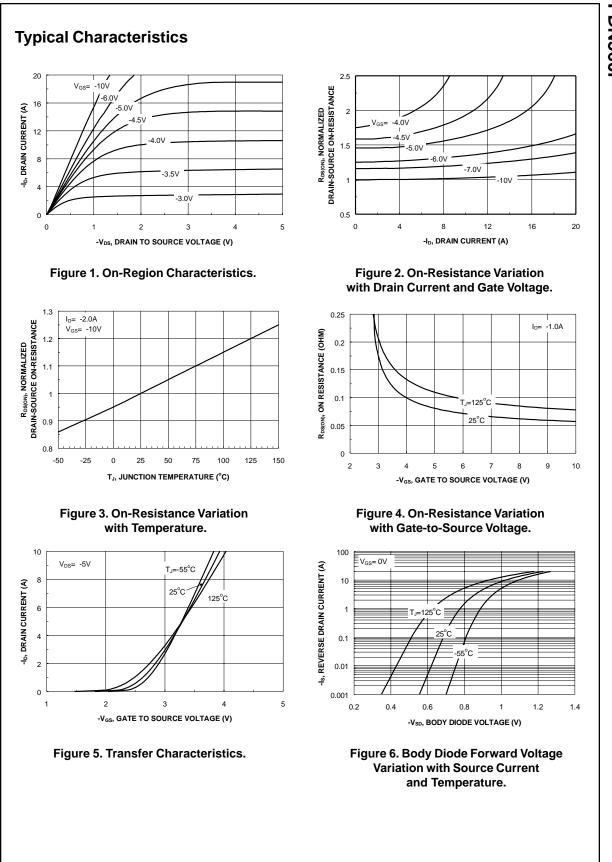
# Package Outlines and Ordering Information

360 FDN360P 7" 8mm 3000 uni	Device Marking	Device	Reel Size	Tape Width	Quantity
	360	FDN360P	7"	8mm	3000 units

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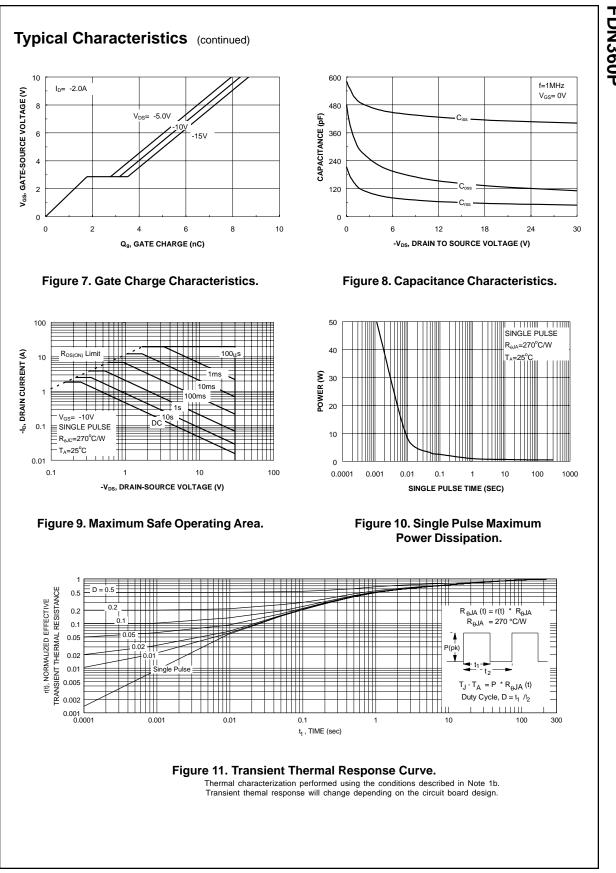
FDN360P

BV <sub>DSS</sub>	Parameter	Test Conditions	Min	Тур	Max	Units
BV <sub>DSS</sub>	acteristics		•			
	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu \text{A}$	-30			V
<u>A</u> BVdss ATJ	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to $25^{\circ}$ C		20		mV/∘C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V},  V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-1	-1.8	-3	V
<u>A</u> VGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to $25 \circ$ C		-4		mV/∘C
R <sub>DS(on)</sub>	Temperature Coefficient $25^{\circ}C$ Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -2 \text{ A}$ On-Resistance $V_{GS} = -10 \text{ V}, I_D = -2 \text{ A}, T_J = 125^{\circ}C$ $V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}$			0.060 0.080 0.095	0.080 0.136 0.125	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -10 \text{ V}, \text{ V}_{DS} = -5 \text{ V}$	-20			Α
<b>g</b> fs	Forward Transconductance $V_{DS} = -5 V$ , $I_D = -2 A$			5.5		S
Dynamic	Characteristics					
C <sub>iss</sub>	Inc Characteristics   Input Capacitance V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V, 420					pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		140		pF
Crss	Reverse Transfer Capacitance	1		60		pF
<u> </u>		1				
	Turn On Dalay Time	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -1 A,	1	0	10	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -15 V, I_D = -1 A,$ $V_{GS} = -10 V, R_{GEN} = 6 \Omega$		9	18	ns
t <sub>r</sub>	Turn-On Rise Time			8	16	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	-		18	29	ns
t <sub>f</sub>	Turn-Off Fall Time			6	12	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = -15 V, I_D = -2 A,$ $V_{GS} = -10 V,$		5	7	nC
Q <sub>gs</sub>	Gate-Source Charge			1.7		nC
().	Gate-Drain Charge 1					nC
Q <sub>gd</sub>	ource Diode Characteristics ar	nd Maximum Ratings				
				1		
	Maximum Continuous Drain-Source D	Diode Forward Current			-0.42	A



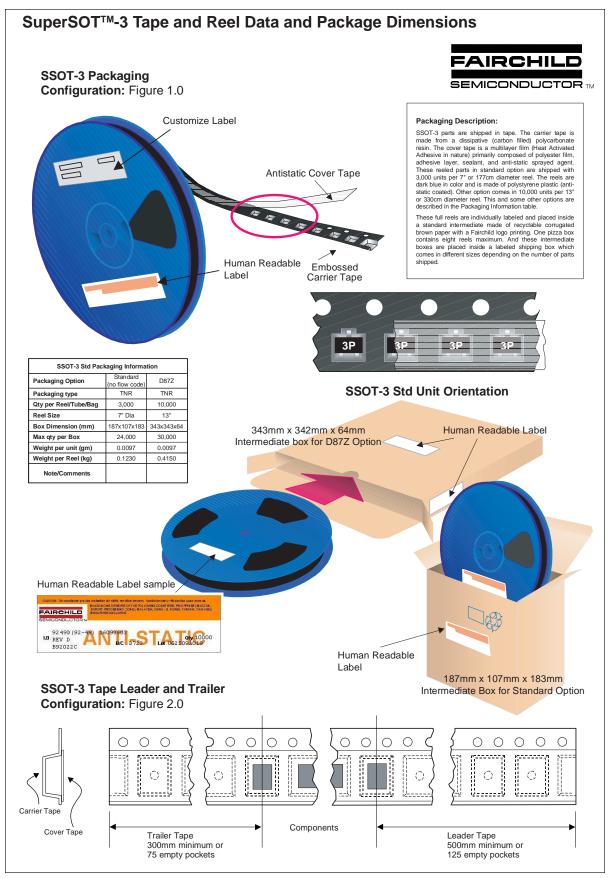
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FDN360P Rev. D

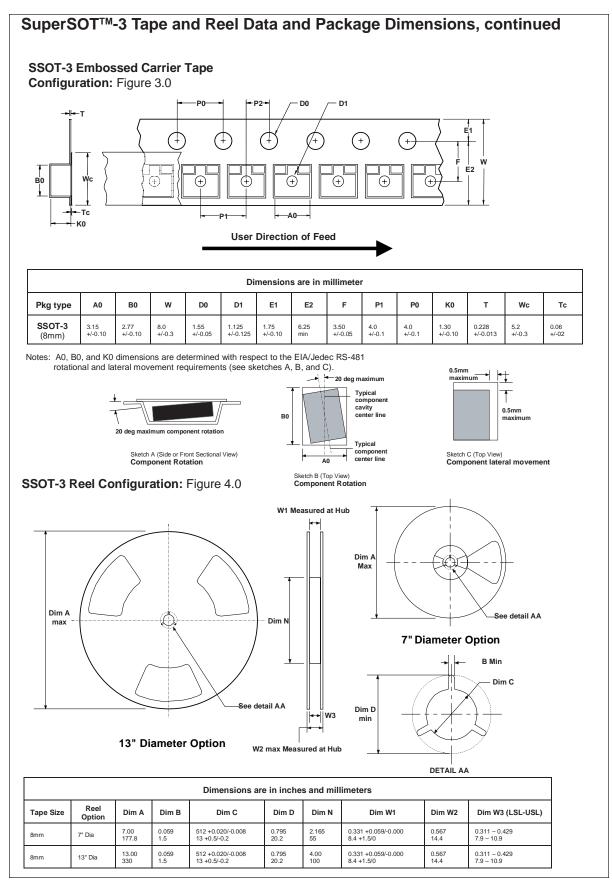


FDN360P Rev. D

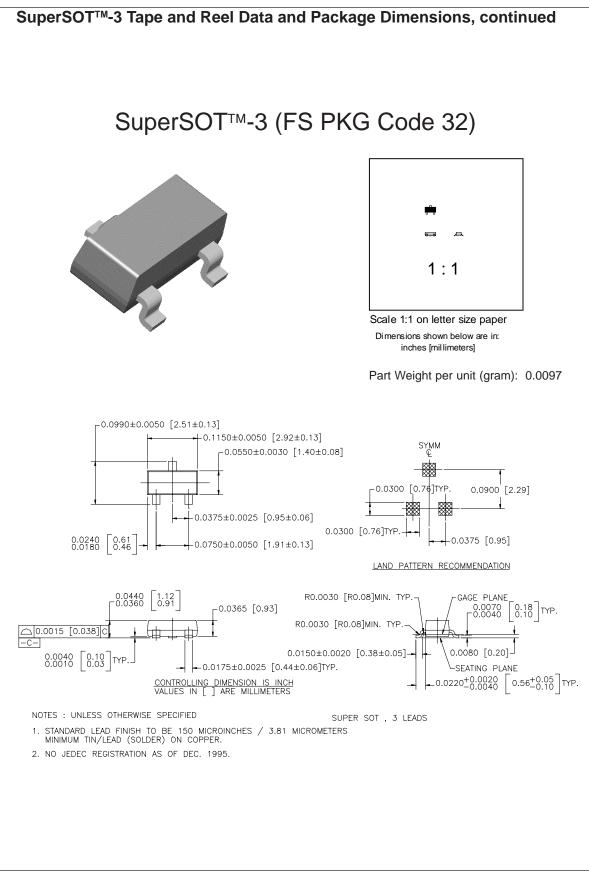
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August 1999, Rev. C



July 1999, Rev. C



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